Title (en)

HIGH PURITY NICKEL/VANADIUM SPUTTERING COMPONENTS; AND METHODS OF MAKING SPUTTERING COMPONENTS

Title (de)

ZERSTÄUBUNGSELEMENTE AUS HOCHREINEM NICKEL/VANADIUM UND VERFAHREN ZUR HERSTELLUNG VON ZERSTÄUBUNGSELEMENTEN

Title (fr)

COMPOSANTS DE PULVERISATION NICKEL/VANADIUM DE PURETE ELEVEE ET PROCEDE DE FABRICATION DE COMPOSANTS DE PULVERISATION

Publication

EP 1579019 A2 20050928 (EN)

Application

EP 03783754 A 20031124

Priority

- US 0337463 W 20031124
- US 43216602 P 20021209

Abstract (en)

[origin: US2004108028A1] The invention includes sputtering components, such as sputtering targets, comprising high-purity Ni-V. The sputtering components can have a fine average grain size throughout, with an exemplary fine average grain size being a grain size less than or equal to 40 microns. The invention also includes methods of making high-purity Ni-V structures.

IPC 1-7

C22C 19/03

IPC 8 full level

C22C 19/03 (2006.01); **C22F 1/10** (2006.01); **C23C 14/00** (2006.01); **C23C 14/34** (2006.01); **C25B 11/00** (2006.01); **H01L 21/203** (2006.01)

IPC 8 main group level

C01G (2006.01)

CPC (source: EP KR US)

C22C 19/03 (2013.01 - EP KR US); **C23C 14/3414** (2013.01 - EP KR US); **H01J 37/3426** (2013.01 - EP KR US)

Citation (search report)

See references of WO 2004052785A2

Designated contracting state (EPC)

DE FR GB NL

DOCDB simple family (publication)

US 2004108028 A1 20040610; AU 2003291159 A1 20040630; AU 2003291159 A8 20040630; CN 1723292 A 20060118; EP 1579019 A2 20050928; JP 2006509109 A 20060316; KR 20050085232 A 20050829; TW 200418996 A 20041001; US 2005230013 A1 20051020; WO 2004052785 A2 20040624; WO 2004052785 A3 20050616; WO 2004052785 B1 20050721

DOCDB simple family (application)

US 72023103 A 20031125; AU 2003291159 A 20031124; CN 200380105352 A 20031124; EP 03783754 A 20031124; JP 2004559157 A 20031124; KR 20057009819 A 20050531; TW 92134690 A 20031209; US 0337463 W 20031124; US 14859605 A 20050608